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(54) **Title:** METHODS FOR GROWING SINGLE CRYSTAL SILICON INGOTS THAT INVOLVE SILICON FEED TUBE INERT GAS CONTROL

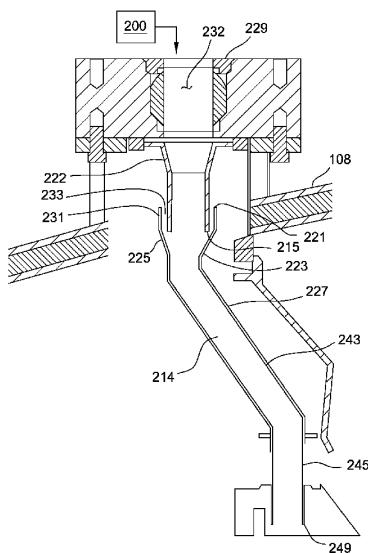


FIG. 6

(57) **Abstract:** Methods for growing single crystal silicon ingots that involve silicon feed tube inert gas control are disclosed. Ingot puller apparatus that include a flange that extends radially from a silicon funnel or from a silicon feed tube to reduce back-flow of gases from the silicon feed tube into the growth chamber are also disclosed.

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